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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

## **Complete if Known**

Sheet	1	of	1	Application Number	10/091,338
				Filing Date	March 6, 2002
				First Named Inventor	Toru MITSUKI et al.
				Group Art Unit	2824
				Examiner Name	Bradley Smith
				Attorney Docket Number	0756-2448

## **U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patent or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Paragraphs or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

## **FOREIGN PATENT DOCUMENTS**

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		Office <sup>2</sup>	Number <sup>2</sup>	Kind Code <sup>2</sup> (if known)				
TSKS		JP	07-162004			06/23/1995		AB
		WO	93-10555			05/27/1993		AB
		JP	04-035021			02/05/1992		AB
		JP	04-286336			10/12/1992		AB

## **OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	†
TSKS		H. Koseki et al., <i>Recent Progress of Low Temperature Poly-Si Technology</i> , Electronic Display Forum, Pages 4-31 to 4-38 and English Translation, Pages 1-21, April 15, 1999.	
TSKS		Kenji Sera et al., <i>Uniformity Improvement of Excimer Laser Crystallized Poly-Si Thin Film Transistors</i> , AM-LCD '96/IDM '96, Pages 85-88.	
TSKS		M. Bonnel et al., <i>Polycrystalline Silicon Thin-Film Transistors with Two-Step Annealing Process</i> , IEEE Electron Device Letters, Vol. 14, No. 12, Pages 551-553, December 1993.	
TSKS		M. Fuse et al., <i>Performance of Poly-Si Thin Film Transistors Fabricated by Excimer-Laser Annealing of SiH<sub>4</sub> and Si<sub>2</sub>H<sub>6</sub> Source Low Pressure Vapor Deposited α-Si Films With or Without Solid-Phase Crystallization</i> , Solid State Phenomena, Vols. 37-38, Pages 565-570, 1994.	

Examiner Signature	<i>TSKS</i>	Date Considered	6/15/04
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